



# HER101 THRU HER108

## HIGH EFFICIENT SILICON RECTIFIER

Reverse Voltage - 50 to 1000 Volts      Forward Current - 1.0 Ampere

### FEATURES

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- Ultra fast switching for high efficiency
- Low reverse leakage
- High forward surge current capability
- High temperature soldering guaranteed:  
250°C/10 seconds, 0.375" (9.5mm) lead length,  
5 lbs. (2.3kg) tension

### MECHANICAL DATA

**Case:** JEDEC DO-41 molded plastic body

**Terminals:** Plated axial leads, solderable per MIL-STD-750, Method 2026

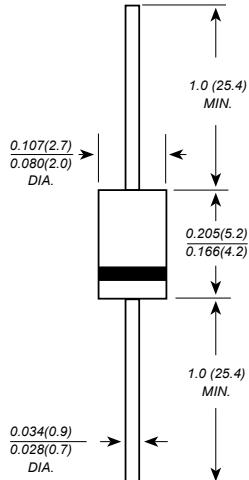
**Polarity:** Color band denotes cathode end

**Mounting Position:** Any

**Weight:** 0.012 ounce, 0.33 grams



DO-41



Dimensions in inches and (millimeters)

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Characteristic	Symbol	HER 101	HER 102	HER 103	HER 104	HER 105	HER 106	HER 107	HER 108	Unit
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>									
Working Peak Reverse Voltage	V <sub>RWM</sub>	50	100	200	300	400	600	800	1000	V
DC Blocking Voltage	V <sub>R</sub>									
RMS Reverse Voltage	V <sub>R(RMS)</sub>	35	70	140	210	280	420	560	700	V
Average Rectified Output Current (Note 1) @T <sub>A</sub> = 55°C	I <sub>O</sub>									A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>									A
Forward Voltage @I <sub>F</sub> = 1.0A	V <sub>FM</sub>				1.0		1.3		1.7	V
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>A</sub> = 100°C	I <sub>RM</sub>					5.0	100			µA
Reverse Recovery Time (Note 2)	t <sub>rr</sub>				50			75		nS
Typical Junction Capacitance (Note 3)	C <sub>j</sub>				20			15		pF
Operating Temperature Range	T <sub>j</sub>				-65 to +150					°C
Storage Temperature Range	T <sub>STG</sub>				-65 to +150					°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

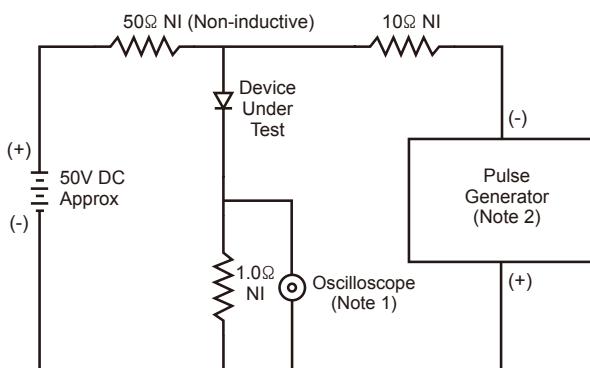
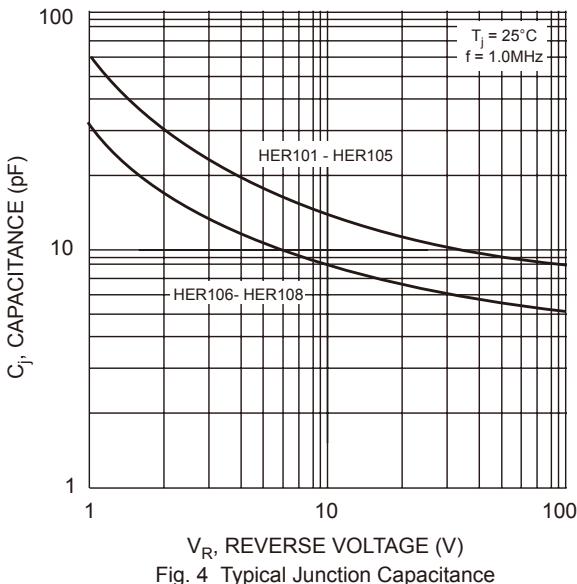
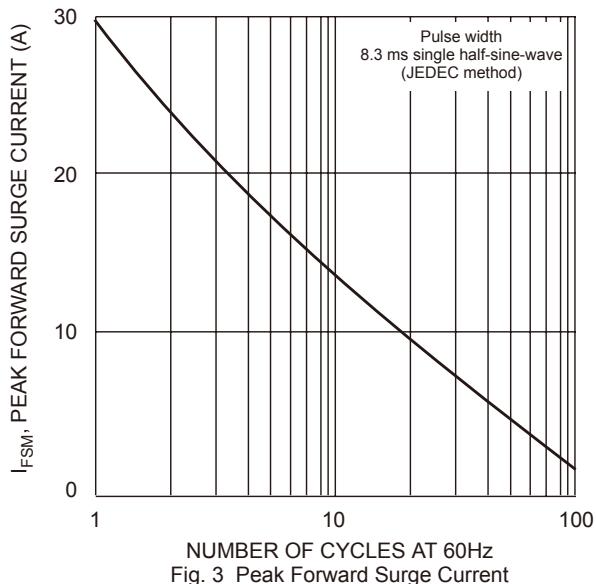
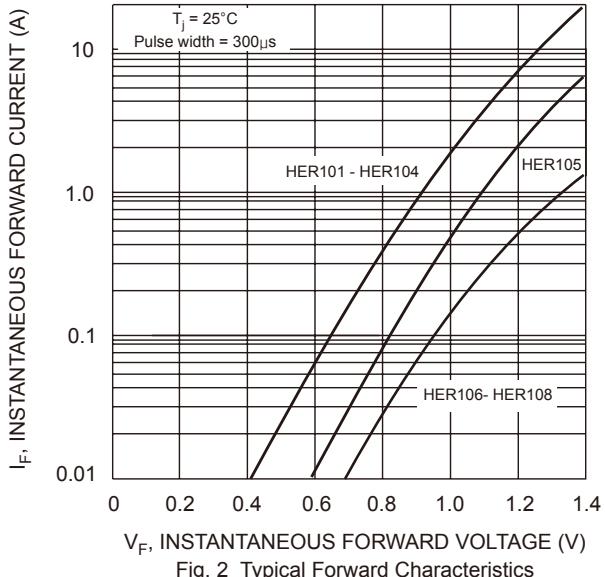
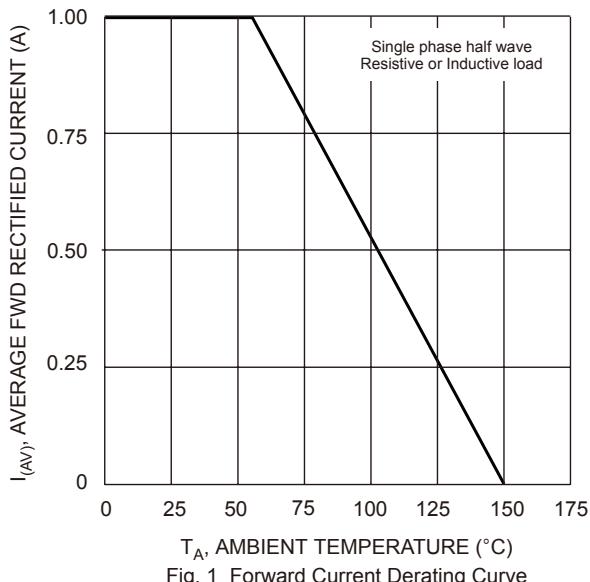
2. Measured with IF = 0.5A, IR = 1.0A, IRR = 0.25A. See figure 5.

3. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.



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## RATINGS AND CHARACTERISTIC CURVES



Notes:

1. Rise Time = 7.0ns max. Input Impedance = 1.0M $\Omega$ , 22pF.
2. Rise Time = 10ns max. Input Impedance = 50 $\Omega$ .

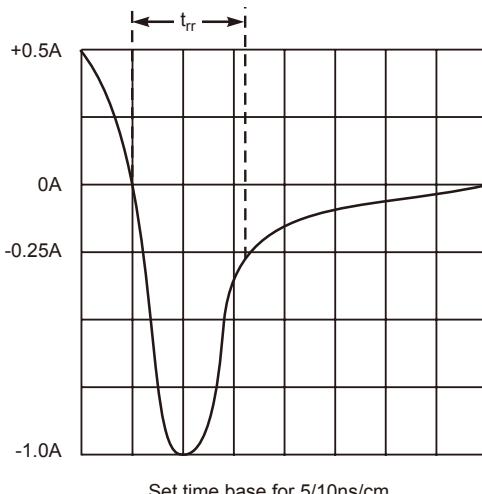


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit